

100397**Quad Differential ECL/TTL Translating Transceiver with Latch****General Description**

The 100397 is a quad latched transceiver designed to convert TTL logic levels to differential F100K ECL logic levels and vice versa. This device was designed with the capability of driving a differential 25Ω ECL load with cutoff capability, and will sink a 64 mA TTL load. The 100397 is ideal for mixed technology applications utilizing either an ECL or TTL backplane.

The direction of translation is set by the direction control pin (DIR). The DIR pin on the 100397 accepts F100K ECL logic levels. An ECL LOW on DIR sets up the ECL pins as inputs and TTL pins as outputs. An ECL HIGH on DIR sets up the TTL pins as inputs and ECL pins as outputs.

A LOW on the output enable input pin (OE) holds the ECL output in a cut-off state and the TTL outputs at a high impedance level. A HIGH on the latch enable input (LE) latches the data at both inputs even though only one output is enabled at the time. A LOW on LE makes the latch transparent.

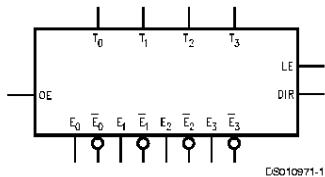
The cut-off state is designed to be more negative than a normal ECL LOW level. This allows the output emitterfollowers

to turn off when the termination supply is $-2.0V$, presenting a high impedance to the data bus. This high impedance reduces termination power and prevents loss of low state noise margin when several loads share the bus.

The 100397 is designed with FAST® TTL output buffers, featuring optimal DC drive and capable of quickly charging and discharging highly capacitive loads. All inputs have $50\text{ K}\Omega$ pull-down resistors.

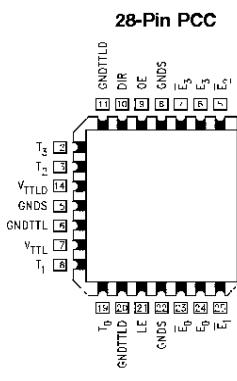
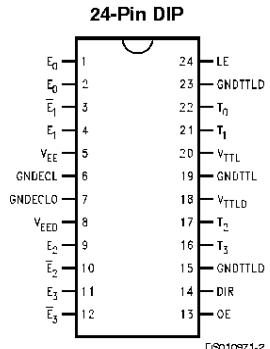
Features

- Differential ECL input/output structure
- 64 mA FAST TTL outputs
- 25Ω differential ECL outputs with cut-off
- Bi-directional translation
- 2000V ESD protection
- Latched outputs
- 3-STATE outputs
- Voltage compensated operating range = $-4.2V$ to $-5.7V$

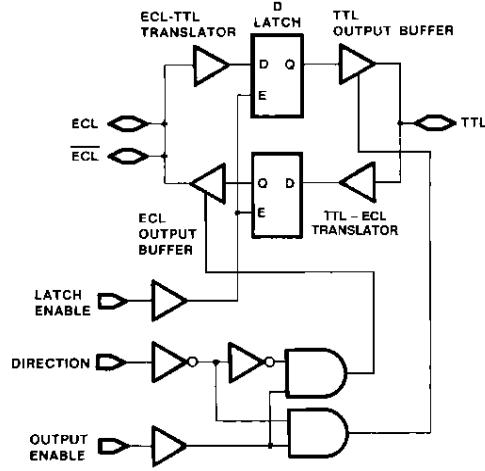
Ordering Code:**Logic Symbol**

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Connection Diagrams



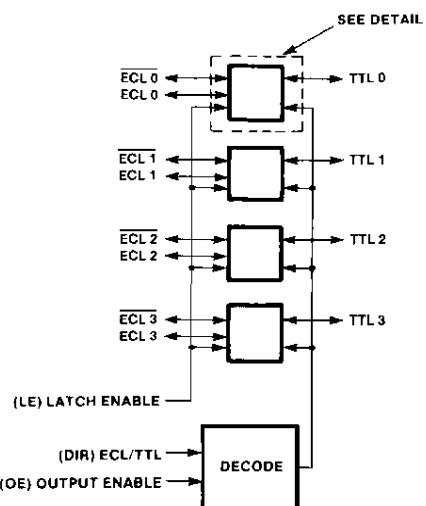
Detail



Pin Names	Description
E ₀ -E ₃	ECL Data I/O
E ₀ -E ₃	Complementary ECL Data I/O
T ₀ -T ₃	TTL Data I/O
OE	Output Enable Input (ECL Levels)
LE	Latch Enable Input (ECL Levels)
DIR	Direction Control Input (ECL levels)
GNDECL	ECL Ground
GNDECLO	ECL Output Ground
GNDS	ECL Ground-to-Substrate
V _{EE}	ECL Quiescent Power Supply
V _{EEED}	ECL Dynamic Power Supply
GNDTTL	TTL Quiescent Ground
GNDTTLD	TTL Dynamic Ground
V _{TTL}	TTL Quiescent Power Supply
V _{TTLD}	TTL Dynamic Power Supply

All pins function at 100K ECL levels except for T₀-T₃

Functional Diagram



Note: LE DIR and OE use ECL logic levels

Truth Table

LE	DIR	OE	ECL Port	TTL Port	Notes
0	0	0	LOW (Cut-Off)	Z	
0	0	1	Input	Output	(Notes 1, 4)
0	1	0	LOW (Cut-Off)	Z	
0	1	1	Output	Input	(Notes 2, 4)
1	0	0	Input	Z	(Notes 1, 3)
1	0	1	Latched	X	(Notes 1, 3)
1	1	0	LOW (Cut-Off)	Input	(Notes 2, 3)
1	1	1	Latched	X	(Notes 2, 3)

H = HIGH Voltage Level

L = LOW Voltage Level

X = Don't Care

Z = High Impedance

Note 1: ECL input to TTL output mode

Note 2: TTL input to ECL output mode

Note 3: Retains data present before LE set HIGH

Note 4: Latch is transparent

Absolute Maximum Ratings (Note 5)

Storage Temperature (T_{STG})	-65°C to +150°C
Maximum Junction Temperature (T_J)	
Ceramic	+175°C
Plastic	+150°C
V_{EE} Pin Potential to Ground Pin	-7.0V to +0.5V
V_{TTL} Pin Potential to Ground Pin	-0.5V to +6.0V
ECL Input Voltage (DC)	V_{EE} to +0.5V
ECL Output Current (DC Output HIGH)	-50 mA
TTL Input Voltage (Note 7)	-0.5V to +7.0V
TTL Input Current (Note 7)	-30 mA to +5.0 mA
Voltage Applied to Output in HIGH State	
3-STATE Output	-0.5V to +5.5V

Current Applied to TTL

Output in LOW State (Max) Twice the Rated I_{OL} (mA)
ESD (Note 6) ≥2000V

Recommended Operating Conditions

Case Temperature (T_C)

Commercial 0°C to +85°C
Industrial -40°C to +85°C
Military -55°C to +125°C

ECL Supply Voltage (V_{EE}) -5.7V to -4.2V
TTL Supply Voltage (V_{TTL}) +4.5V to +5.5V

Note 5: Absolute maximum ratings are those values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 6: ESD testing conforms to MIL-STD-883 Method 3015

Note 7: Either voltage limit or current limit is sufficient to protect inputs

Commercial Version

TTL-to-ECL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, GND = 0V, $T_C = 0^\circ C$ to $+85^\circ C$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 8)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output HIGH Voltage	-1025	-955	-870	mV	$V_{IN} = V_{IH(\text{Max})}$ or $V_{IL(\text{Min})}$
V_{OL}	Output LOW Voltage	-1830	-1705	-1620	mV	Loading with 50Ω to $-2V$
	Cutoff Voltage			-2000	mV	OE and LE Low, DIR High
				-1950	mV	$V_{IN} = V_{IH(\text{Max})}$ or $V_{IL(\text{Min})}$, Loading with 50Ω to $-2V$
V_{OHC}	Output HIGH Voltage Corner Point High	-1035			mV	$V_{IN} = V_{IH(\text{Min})}$ or $V_{IL(\text{Max})}$
V_{OLC}	Output LOW Voltage Corner Point Low			-1610	mV	Loading with 50Ω to $-2V$
V_{IH}	Input HIGH Voltage	2.0		5.0	V	Over V_{TTL} , V_{EE} , T_C Range
V_{IL}	Input LOW Voltage	0		0.8	V	Over V_{TTL} , V_{EE} , T_C Range
I_{IH}	Input HIGH Current			5.0	μA	$V_{IN} = +2.7V$
I_{BVIT}	Input HIGH Current Breakdown (I/O)			0.5	mA	$V_{IN} = 5.5V$
I_{IL}	Input LOW Current	-1.0			mA	$V_{IN} = +0.5V$
V_{FCD}	Input Clamp Diode Voltage	-1.2			V	$I_{IN} = -18\text{ mA}$
I_{EE}	V_{EE} Supply Current	-99		-50		LE Low, OE and DIR High Inputs Open
I_{EEZ}	V_{EE} Supply Current	-159		-90		LE and OE Low, Dir High Inputs Open

Note 8: The specified limits represent the "worst case" value for the parameter. Since these values normally occur at the temperature extremes, additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under "worst case" conditions.

ECL-to-TTL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, GND = 0V, $T_C = 0^\circ C$ to $+85^\circ C$, $C_L = 50\text{ pF}$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 9)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output HIGH Voltage	2.7	3.1		V	$I_{OH} = -3\text{ mA}$, $V_{TTL} = 4.75V$
		2.4	2.9		V	$I_{OH} = -3\text{ mA}$, $V_{TTL} = 4.50V$
V_{OL}	Output LOW Voltage		0.3	0.5	V	$I_{OL} = 24\text{ mA}$, $V_{TTL} = 4.50V$

ECL-to-TTL DC Electrical Characteristics (Continued)

$V_{EE} = -4.2V$ to $-5.7V$, $GND = 0V$, $T_C = 0^\circ C$ to $+85^\circ C$, $C_L = 50 \text{ pF}$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 9)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{IH}	Input HIGH Voltage	-1165		-870	mV	Guaranteed HIGH Signal for All Inputs
V_{IL}	Input LOW Voltage	-1830		-1475	mV	Guaranteed LOW Signal for All Inputs
V_{DIFF}	Input Voltage Differential	150			mV	Required for Full Output Swing
V_{CM}	Common Mode Voltage	GNDECL - 2.0		GNDECL - 0.5	V	
I_{IH}	Input HIGH Current $E_o-E_3, \bar{E}_o-\bar{E}_3$ OE, LE, DIR			240 35	μA	$V_{IN} = V_{IH(\text{Max})}$
I_{CEX}	Output HIGH Leakage Current			50	μA	$V_{OUT} = V_{TTL}$
I_{ZZ}	Bus Drainage Test			500	μA	$V_{OUT} = 5.25V$ $V_{TTL} = 0.0V$
I_{IL}	Input LOW Current	0.50			μA	$V_{IN} = V_{IL(\text{Min})}$
I_{OZHT}	3-STATE Current Output High			70	μA	$V_{OUT} = +2.7V$
I_{OZLT}	3-STATE Current Output Low	-650			μA	$V_{OUT} = +0.5V$
I_{OS}	Output Short-Circuit Current	-100		-225	mA	$V_{OUT} = 0.0V, V_{TTL} = +5.5V$
I_{TTL}	V_{TTL} Supply Current			39 27 39	mA	TTL Outputs LOW TTL Outputs HIGH TTL Outputs in 3-STATE

Note 9: The specified limits represent the "worst case" value for the parameter. Since these values normally occur at the temperature extremes additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under "worst case" conditions.

DIP and PCC TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	$T_C = 0^\circ C$		$T_C = 25^\circ C$		$T_C = 85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
F_{Max}	Maximum Clock Frequency	180		180		180		MHz	
t_{PLH}	T_n to E_n, \bar{E}_n (Transparent)	0.9	2.1	0.8	2.2	0.7	2.5	ns	Figures 1, 3
t_{PHL}	LE to E_n, \bar{E}_n	1.2	2.3	1.3	2.4	1.4	2.5	ns	Figures 1, 3
t_{PZH}	OE to E_n, \bar{E}_n (Cutoff to High)	2.5	4.5	2.5	4.5	2.5	4.6	ns	Figures 1, 3
t_{PHZ}	OE to E_n, \bar{E}_n (High to Cutoff)	2.1	3.8	2.3	4.0	2.5	4.5	ns	Figures 1, 3
t_{PHZ}	DIR to E_n, \bar{E}_n (High to Cutoff)	2.0	3.5	2.1	3.7	2.3	4.2	ns	Figures 1, 3
t_s	T_n to LE	0.8		0.8		0.8		ns	Figures 1, 3
t_h	T_n to LE	0.6		0.6		0.6		ns	Figures 1, 3
t_{TLH}	Transition Time 20% to 80%, 80% to 20%	0.8	2.8	0.8	2.8	0.8	2.8	ns	Figures 1, 3

DIP and PCC ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $C_L = 50\text{ pF}$

Symbol	Parameter	$T_C = 0^\circ\text{C}$		$T_C = 25^\circ\text{C}$		$T_C = 85^\circ\text{C}$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
F_{Max}	Maximum Clock Frequency	75		75		75		MHz	
t_{PLH}	E_n, \bar{E}_n to T_n (Transparent)	1.7	4.9	1.7	5.1	1.8	5.8	ns	Figures 2, 4
t_{PHL}	LE to T_n	2.2	4.0	2.2	4.0	2.3	4.1	ns	Figures 2, 4
t_{PLH}	E_n, \bar{E}_n to T_n (Enable Time)	3.3	5.2	3.4	5.4	3.8	6.1	ns	Figures 2, 5
t_{PZH}	OE to T_n	3.2	5.6	3.3	5.7	3.6	6.3	ns	Figures 2, 5
t_{PZL}	E_n, \bar{E}_n to T_n (Disable Time)	4.9	8.3	5.1	8.5	5.6	9.2	ns	Figures 2, 5
t_{PHZ}	OE to T_n	3.6	8.6	3.5	8.3	3.5	7.5	ns	Figures 2, 5
t_{PLZ}	E_n, \bar{E}_n to LE (Disable Time)	3.4	6.9	3.5	6.7	3.6	6.7	ns	Figures 2, 6
t_S	E_n, \bar{E}_n to LE	0.6		0.6		0.6		ns	Figures 2, 4
t_H	E_n, \bar{E}_n to LE	0.7		0.7		0.7		ns	Figures 2, 4
$t_{PW(L)}$	Pulse Width LE	2.0		2.0		2.0		ns	Figures 2, 4

Industrial Version

TTL-to-ECL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $GND = 0V$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 10)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output HIGH Voltage	-1085	-955	-870	mV	$V_{IN} = V_{IH(\text{Max})}$ or $V_{IL(\text{Min})}$
V_{OL}	Output LOW Voltage	-1830	-1705	-1575	mV	Loading with 50Ω to $-2V$
	Cutoff Voltage		-2000	-1900	mV	OE and LE Low, DIR High $V_{IN} = V_{IH(\text{Max})}$ or $V_{IL(\text{Min})}$ Loading with 50Ω to $-2V$
V_{OHC}	Output HIGH Voltage Corner Point High	-1095			mV	$V_{IN} = V_{IH(\text{Min})}$ or $V_{IL(\text{Max})}$ Loading with 50Ω to $-2V$
V_{OLC}	Output LOW Voltage Corner Point Low			-1565	mV	
V_{IH}	Input HIGH Voltage	2.0		5.0	V	Over V_{TTL}, V_{EE}, T_C Range
V_{IL}	Input LOW Voltage	0		0.8	V	Over V_{TTL}, V_{EE}, T_C Range
I_{IH}	Input HIGH Current			5.0	μA	$V_{IN} = +2.7V$
I_{BVIT}	Input HIGH Current Breakdown (I/O)			0.5	mA	$V_{IN} = 5.5V$
I_{IL}	Input LOW Current	-1.0			mA	$V_{IN} = +0.5V$
V_{FCD}	Input Clamp Diode Voltage	-1.2			V	$I_{IN} = -18\text{ mA}$
I_{EE}	V_{EE} Supply Current	-99		-40		LE Low, OE and DIR High Inputs Open
I_{EEZ}	V_{EE} Supply Current	-159		-90		LE and OE Low, Dir High Inputs Open

Note 10: The specified limits represent the "worst case" value for the parameter. Since these values normally occur at the temperature extremes additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under "worst case" conditions.

ECL-to-TTL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{GND} = 0V$, $T_C = -40^\circ C$ to $+85^\circ C$, $C_L = 50 \text{ pF}$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 11)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output HIGH Voltage	2.7	3.1		V	$I_{OH} = -3 \text{ mA}$, $V_{TTL} = 4.75V$
		2.4	2.9		V	$I_{OH} = -3 \text{ mA}$, $V_{TTL} = 4.50V$
V_{OL}	Output LOW Voltage		0.3	0.5	V	$I_{OL} = 24 \text{ mA}$, $V_{TTL} = 4.50V$
V_{IH}	Input HIGH Voltage	-1170		-870	mV	Guaranteed HIGH Signal for All Inputs
V_{IL}	Input LOW Voltage	-1830		-1480	mV	Guaranteed LOW Signal for All Inputs
V_{DIFF}	Input Voltage Differential	150			mV	Required for Full Output Swing
V_{CM}	Common Mode Voltage	GNDECL - 2.0		GNDECL - 0.5	V	
I_{IH}	Input HIGH Current $E_o - E_a, \bar{E}_o - \bar{E}_a$ OE, LE, DIR			300 35	µA	$V_{IN} = V_{IH(\text{Max})}$
I_{CEX}	Output HIGH Leakage Current			50	µA	$V_{OUT} = V_{TTL}$
I_{ZZ}	Bus Drainage Test			500	µA	$V_{OUT} = 5.25V$ $V_{TTL} = 0.0V$
I_{IL}	Input LOW Current	0.50			µA	$V_{IN} = V_{IL(\text{Min})}$
I_{OZHT}	3-STATE Current Output High			70	µA	$V_{OUT} = +2.7V$
I_{OZLT}	3-STATE Current Output Low	-650			µA	$V_{OUT} = +0.5V$
I_{OS}	Output Short-Circuit Current	-100		-225	mA	$V_{OUT} = 0.0V, V_{TTL} = +5.5V$
I_{TTL}	V_{TTL} Supply Current			39 27 39	mA	TTL Outputs LOW TTL Outputs HIGH TTL Outputs in 3-STATE

Note 11: The specified limits represent the "worst case" value for the parameter. Since these values normally occur at the temperature extremes, additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under "worst case" conditions.

PCC TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	$T_c = -40^\circ C$		$T_c = +25^\circ C$		$T_c = +85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
F_{Max}	Maximum Clock Frequency	180		180		180		MHz	
t_{PLH}	T_n to E_n, \bar{E}_n (Transparent)	0.9	2.4	0.8	2.2	0.7	2.5	ns	Figures 1, 3
t_{PHL}	LE to E_n, \bar{E}_n	1.2	2.3	1.3	2.4	1.4	2.5	ns	Figures 1, 3
t_{PZH}	OE to E_n, \bar{E}_n (Cutoff to High)	1.9	3.8	2.5	4.5	2.5	4.6	ns	Figures 1, 3
t_{PHZ}	OE to E_n, \bar{E}_n (High to Cutoff)	2.5	4.7	2.3	4.0	2.5	4.5	ns	Figures 1, 3
t_{PHZ}	DIR to E_n, \bar{E}_n (High to Cutoff)	1.8	3.5	2.1	3.7	2.3	4.2	ns	Figures 1, 3
t_s	T_n to LE	0.8		0.8		0.8		ns	Figures 1, 3
t_h	T_n to LE	0.6		0.6		0.6		ns	Figures 1, 3
t_{TLH}	Transition Time 20% to 80%, 80% to 20%	0.8	2.8	0.8	2.8	0.8	2.8	ns	Figures 1, 3

PCC ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $C_L = 50\text{ pF}$

Symbol	Parameter	$T_C = -40^\circ\text{C}$		$T_C = +25^\circ\text{C}$		$T_C = +85^\circ\text{C}$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
F_{Max}	Maximum Clock Frequency	75		75		75		MHz	
t_{PLH}	E_n, \bar{E}_n to T_n (Transparent)	1.7	4.9	1.7	5.1	1.8	5.8	ns	Figures 2, 4
t_{PHL}	LE to T_n	2.2	4.3	2.2	4.0	2.3	4.1	ns	Figures 2, 4
t_{PHL}		3.3	5.2	3.4	5.4	3.8	6.1	ns	Figures 2, 4
t_{PZH}	OE to T_n	3.1	5.6	3.3	5.7	3.6	6.3	ns	Figures 2, 5
t_{PZL}	(Enable Time)	4.8	8.3	5.1	8.5	5.6	9.2	ns	Figures 2, 5
t_{PHZ}	OE to T_n	3.5	9.2	3.5	8.3	3.5	7.5	ns	Figures 2, 5
t_{PLZ}	(Disable Time)	3.2	7.3	3.5	6.7	3.6	6.7	ns	Figures 2, 5
t_{PHZ}	DIR to T_n	3.5	8.8	3.5	8.1	3.5	7.6	ns	Figures 2, 6
t_{PLZ}	(Disable Time)	3.2	7.2	3.4	6.7	3.6	6.7	ns	Figures 2, 6
t_S	E_n, \bar{E}_n to LE	0.6		0.6		0.6		ns	Figures 2, 4
t_H	E_n, \bar{E}_n to LE	0.7		0.7		0.7		ns	Figures 2, 4
$t_{PW(L)}$	Pulse Width LE	2.0		2.0		2.0		ns	Figures 2, 4

Military Version—Preliminary TTL-to-ECL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $GND = 0V$, $T_C = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	Min	Max	Units	T_C	Conditions		Notes	
V_{OH}	Output HIGH Voltage	-1025	-870	mV	0°C to +125°C	$V_{IN} = V_{IH}$ (Max) or V_{IL} (Min)	Loading with 50Ω to -2.0V	(Notes 12, 13, 14)	
		-1085	-870	mV	-55°C				
V_{OL}	Output LOW Voltage	-1830	-1620	mV	0°C to +125°C	OE or DIR Low			
		-1830	-1555	mV	-55°C				
V_{OHC}	Output HIGH Voltage	-1035		mV	0°C to +125°C	$V_{IN} = V_{IH}$ (Min) or V_{IL} (Max)	Loading with 50Ω to -2.0V	(Notes 12, 13, 14)	
		-1085		mV	-55°C				
V_{OLC}	Output LOW Voltage		-1610	mV	0°C to +125°C				
			-1555	mV	-55°C				
V_{IH}	Input HIGH Voltage	2.0		V	-55°C to +125°C	Over V_{TTL}, V_{EE}, T_C Range		(Notes 12, 13, 14, 15)	
V_{IL}	Input LOW Voltage		0.8	V	-55°C to +125°C	Over V_{TTL}, V_{EE}, T_C Range		(Notes 12, 13, 14, 15)	
I_{IH}	Input HIGH Current		70	μA	-55°C to 125°C	$V_{IN} = +2.7V$		(Notes 12, 13, 14)	
	Breakdown Test		1.0	mA	-55°C to +125°C	$V_{IN} = +5.5V$			
I_{IL}	Input LOW Current	-1.0		mA	-55°C to +125°C	$V_{IN} = +0.5V$		(Notes 12, 13, 14)	
V_{FCD}	Input Clamp Diode Voltage	-1.2		V	-55°C to +125°C	$I_{IN} = -18\text{ mA}$		(Notes 12, 13, 14)	

Military Version—Preliminary TTL-to-ECL DC Electrical Characteristics (Continued)

$V_{EE} = -4.2V$ to $-5.7V$, $GND = 0V$, $T_C = -55^{\circ}C$ to $+125^{\circ}C$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	Min	Max	Units	T_c	Conditions	Notes
I_{EE}	V_{EE} Supply Current			mA	$-55^{\circ}C$ to $+125^{\circ}C$	LE Low, OE and DIR High Inputs Open $V_{EE} = -4.2V$ to $-4.8V$ $V_{EE} = -4.2V$ to $-5.7V$	(Notes 12, 13, 14)
		-165	-65				
		-175	-65				

ECL-to-TTL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $GND = 0V$, $T_C = -55^{\circ}C$ to $+125^{\circ}C$, $C_L = 50 pF$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	Min	Max	Units	T_c	Conditions	Notes
V_{OH}	Output HIGH Voltage	2.5		mV	$0^{\circ}C$ to $+125^{\circ}C$	$I_{OH} = -1 mA$, $V_{TTL} = 4.50V$	
		2.4			$-55^{\circ}C$	$I_{OH} = -3 mA$, $V_{TTL} = 4.50V$	
V_{OL}	Output LOW Voltage		0.5	mV	$-55^{\circ}C$ to $+125^{\circ}C$	$I_{OL} = 24 mA$, $V_{TTL} = 4.50V$	(Notes 12, 13, 14)
V_{IH}	Input HIGH Voltage	-1165	-870	mV	$-55^{\circ}C$ to $+125^{\circ}C$	Guaranteed HIGH Signal for All Inputs	(Notes 12, 13, 14, 15)
V_{IL}	Input LOW Voltage	-1830	-1475	mV	$-55^{\circ}C$ to $+125^{\circ}C$	Guaranteed LOW Signal for All Inputs	(Notes 12, 13, 14, 15)
I_{IH}	Input HIGH Current		350	μA	$0^{\circ}C$ to $+125^{\circ}C$	$V_{EE} = -5.7V$	(Notes 12, 13, 14)
			500			$V_{IN} = V_{IH(Max)}$	
I_{IL}	Input LOW Current	0.50		μA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{EE} = -4.2V$	(Notes 12, 13, 14)
						$V_{IN} = V_{IL(Min)}$	
I_{OZHT}	3-STATE Current Output High		70	μA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = +2.7V$	(Notes 12, 13, 14)
I_{OZLT}	3-STATE Current Output Low	-1.0		mA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = +0.5V$	(Notes 12, 13, 14)
I_{OS}	Output Short-Circuit CURRENT	-150	-60	mA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = 0.0V$, $V_{TTL} = +5.5V$	(Notes 12, 13, 14)
I_{TTL}	V_{TTL} Supply Current		75	mA	$-55^{\circ}C$ to $+125^{\circ}C$	TTL Outputs Low TTL Output High TTL Output in 3-STATE	(Notes 12, 13, 14)
			50	mA			
			70	mA			

Note 12: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals $-55^{\circ}C$) then testing immediately without allowing for the junction temperature to stabilize due to heat dissipation after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 13: Screen tested 100% on each device at $-55^{\circ}C$, $+25^{\circ}C$, and $+125^{\circ}C$. Subgroups 1 2 3 7 and 8

Note 14: Sample tested (Method 5005 Table I) on each manufactured lot at $-55^{\circ}C$, $+25^{\circ}C$, and $+125^{\circ}C$. Subgroups A1 2 3 7 and 8

Note 15: Guaranteed by applying specified input condition and testing V_{OH}/V_{OL} .

TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$

Symbol	Parameter	$T_c = -55^{\circ}C$		$T_c = +25^{\circ}C$		$T_c = +125^{\circ}C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PLH} t_{PHL}	T_n to E_n , \bar{E}_n (Transparent)	1.0	3.9	1.1	3.6	1.1	4.0	ns	<i>Figures 1, 2</i>	(Notes 12, 13, 14)
	LE to E_n , \bar{E}_n	1.2	3.8	1.4	3.7	1.6	4.2	ns	<i>Figures 1, 2</i>	
t_{PLH} t_{PHL}										

TTL-to-ECL AC Electrical Characteristics (Continued)

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$

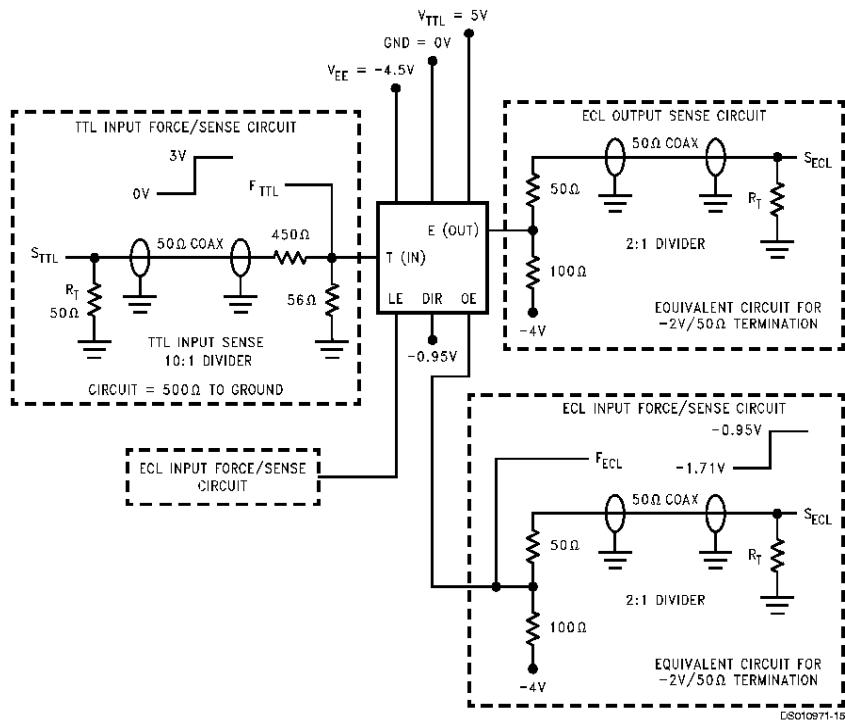
Symbol	Parameter	$T_C = -55^\circ C$		$T_C = +25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PZH}	OE to E_n, \bar{E}_n (Cutoff to HIGH)	1.0	4.3	1.5	4.4	1.7	5.2	ns	<i>Figures 1, 2</i>	(Notes 12, 13, 14)
t_{PHZ}	OE to E_n, \bar{E}_n (HIGH to Cutoff)	1.5	5.1	1.6	4.5	1.6	5.1	ns	<i>Figures 1, 2</i>	
t_{PHZ}	DIR to E_n, \bar{E}_n (HIGH to Cutoff)	1.6	4.7	1.6	4.3	1.7	4.9	ns	<i>Figures 1, 2</i>	
t_{set}	T_n to LE	2.5		2.0		2.5		ns	<i>Figures 1, 2</i>	(Note 15)
t_{hold}	T_n to LE	2.5		2.0		2.5		ns	<i>Figures 1, 2</i>	
$t_{pw(H)}$	Pulse Width LE	2.5		2.0		2.5		ns	<i>Figures 1, 2</i>	(Note 15)
t_{TLH}	Transition Time 20% to 80%, 80% to 20%	0.4	2.3	0.5	2.1	0.4	2.4	ns	<i>Figures 1, 2</i>	(Note 15)
t_{THL}										

ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $GND = 0V$, $C_L = 50 pF$

Symbol	Parameter	$T_C = -55^\circ C$		$T_C = 25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PLH}	E_n, \bar{E}_n to T_n (Transparent)	2.3	6.4	2.4	5.6	2.6	6.3	ns	<i>Figures 3, 4</i>	(Notes 12, 13, 14)
t_{PLH}	LE to T_n	3.1	8.0	3.1	7.3	3.3	8.0	ns	<i>Figures 3, 4</i>	
t_{PHL}										
t_{PZH}	OE to T_n (Enable Time)	3.2	8.9	3.7	9.0	4.0	10.2	ns	<i>Figures 3, 5</i>	(Notes 12, 13, 14)
t_{PZL}		3.6	9.4	4.0	9.3	4.3	10.4			
t_{PHZ}	OE to T_n	3.2	9.9	3.3	9.0	3.5	9.4	ns	<i>Figures 3, 5</i>	
t_{PLZ}	(Disable Time)	3.0	9.7	3.4	8.8	4.1	10.6			
t_{PHZ}	DIR to T_n	2.6	9.4	2.8	8.8	2.9	9.1	ns	<i>Figures 3, 6</i>	
t_{PLZ}	(Disable Time)	2.7	8.5	3.1	8.0	4.0	9.7			
t_{set}	E_n, \bar{E}_n to LE	2.5		2.0		2.5		ns	<i>Figures 3, 4</i>	(Note 15)
t_{hold}	E_n, \bar{E}_n to LE	3.0		2.5		3.0		ns	<i>Figures 3, 4</i>	
$t_{pw(H)}$	Pulse Width LE	2.5		2.0		5.0		ns	<i>Figures 3, 4</i>	(Note 15)

Test Circuitry (TTL-to-ECL)



Notes:

$R_t = 50\Omega$ termination. When an input or output is being monitored by a scope, R_t is supplied by the scope's 50Ω resistance. When an input or output is not being monitored, and external 50Ω resistance must be applied to serve as R_t .
 TTL and ECL force signals are brought to the DUT via 50Ω coax lines.
 V_{TTL} is decoupled to ground with $0.1\ \mu F$ to ground. V_{EE} is decoupled to ground with $0.01\ \mu F$ and GND is connected to ground.
 For ECL input pins, the equivalent force/sense circuitry is optional.

FIGURE 1. TTL-to-ECL AC Test Circuit

Switching Waveforms (TTL-to-ECL)

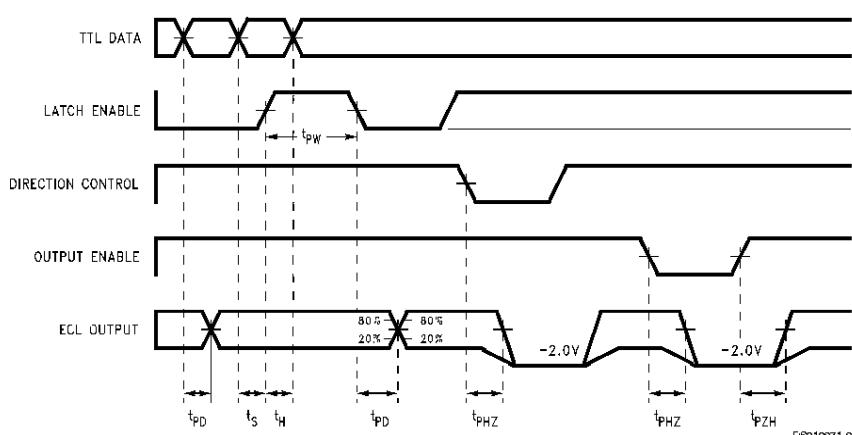
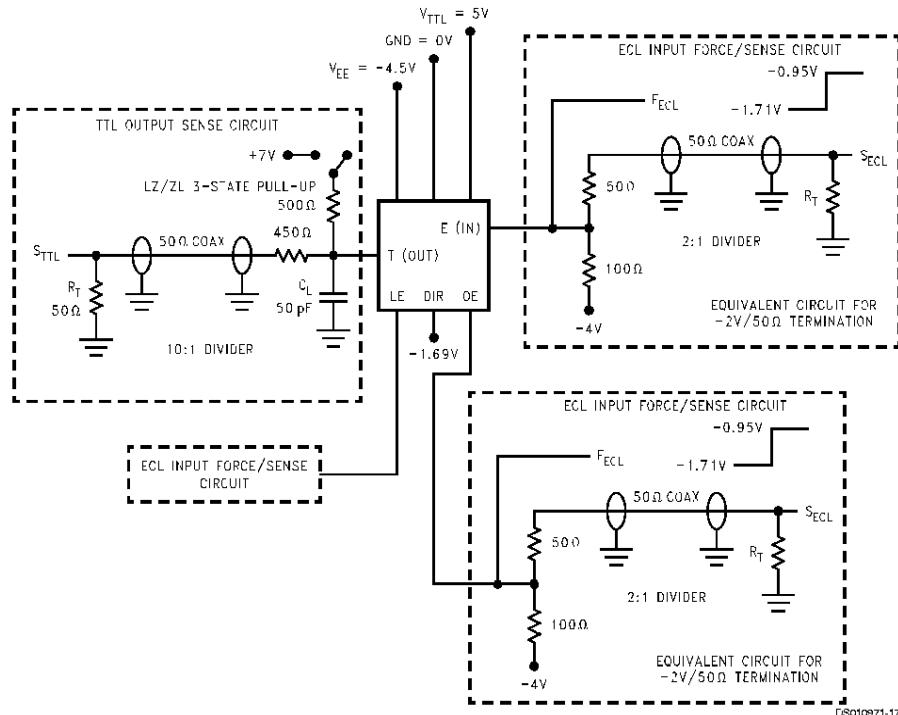


FIGURE 2. TTL to ECL Transition—Propagation Delay and Transition Times

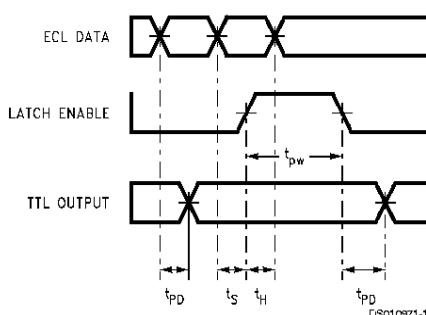
Test Circuitry (ECL-to-TTL)



Notes:

$R_t = 50\Omega$ termination. When an input or output is being monitored by a scope, R_t is supplied by the scope's 50Ω resistance. When an input or output is not being monitored, and external 50Ω resistance must be applied to serve as R_t .
The TTL 3-STATE pull up switch is connected to +7V only for ZL and LZ tests.
TTL and ECL force signals are brought to the DUT via 50Ω coax lines.
 V_{TTL} is decoupled to ground with $0.1\ \mu F$ and GND is connected to ground.

FIGURE 3. ECL-to-TTL AC Test Circuit

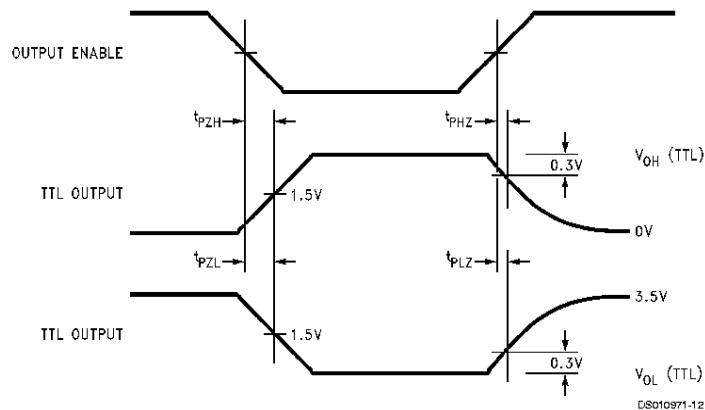


Note:

DIR is LOW and OE is HIGH

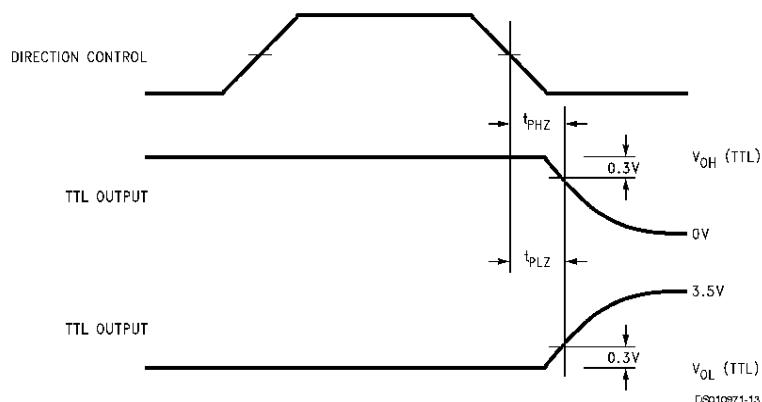
FIGURE 4. ECL-to-TTL Transition—Propagation Delay and Transition Times

Test Circuitry (ECL-to-TTL) (Continued)



Note:
DIR is LOW LE is HIGH

FIGURE 5. ECL-to-TTL Transition, OE to TTL Output, Enable and Disable Times



Note:
OE is HIGH LE is HIGH

FIGURE 6. ECL-to-TTL Transition, DIR to TTL Output, Disable Time

Applications

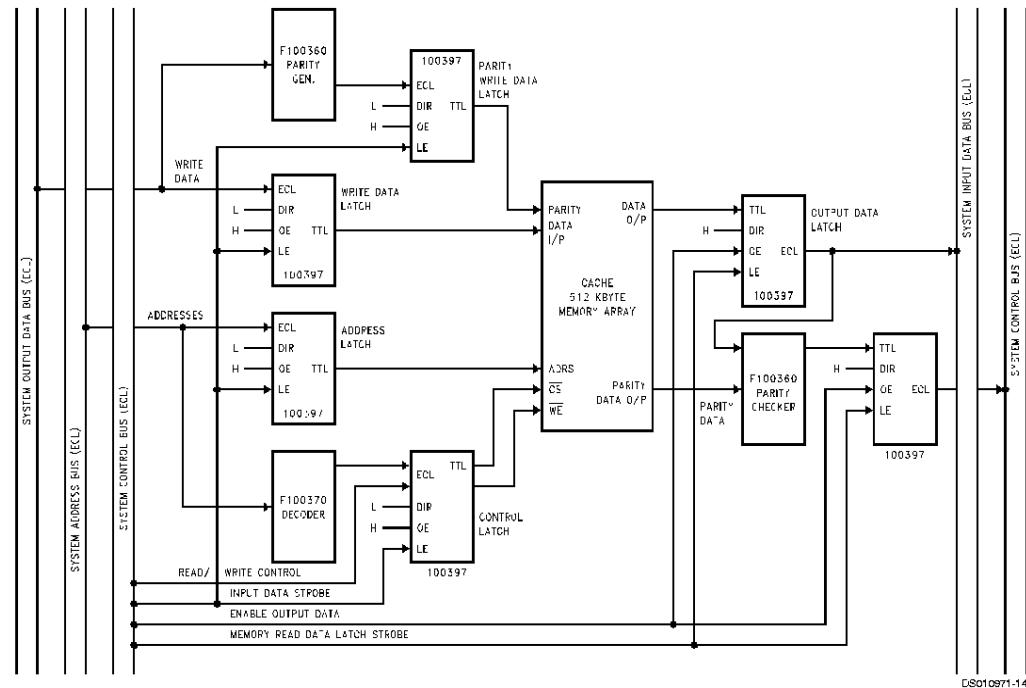
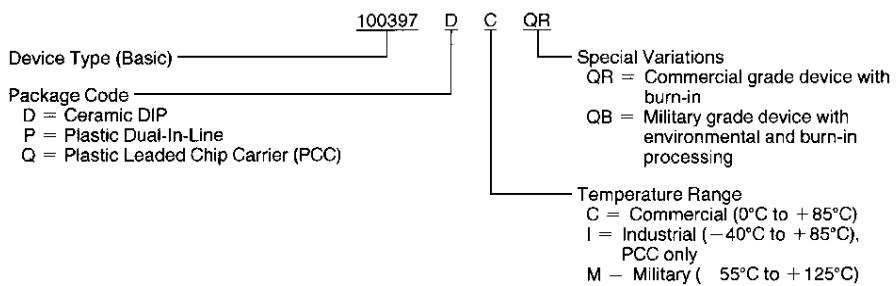


FIGURE 7. Applications Diagram—MOS/TTL SRAM Interface Using 100397 ECL-TTL Latched Translator

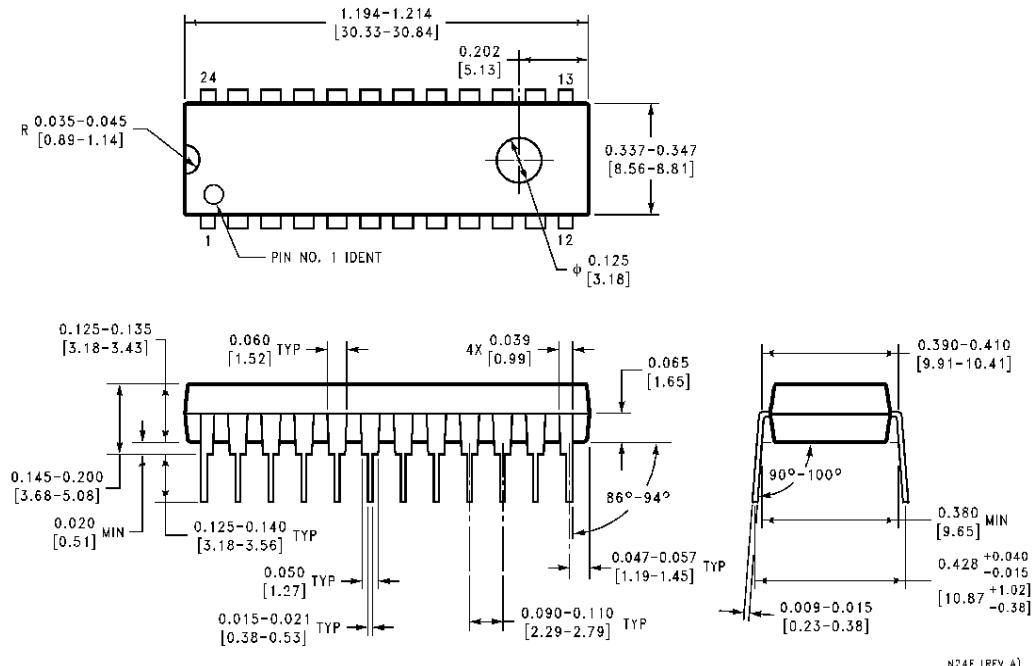
Ordering Information

The device number is used to form part of a simplified purchasing code where A package type and temperature range are defined as follows:



DS010971-16

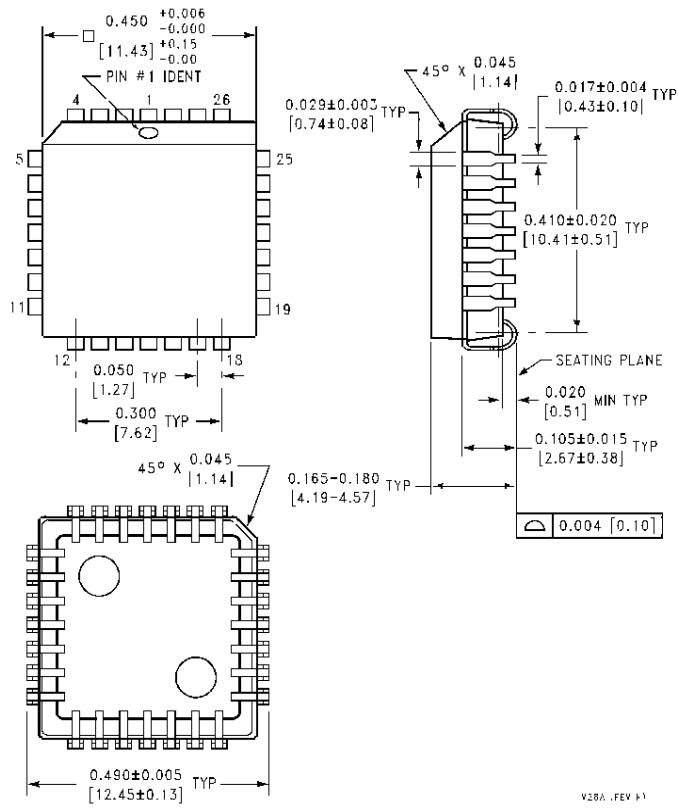
Physical Dimensions inches (millimeters) unless otherwise noted



**24-Lead Plastic Dual-In-Line Package (0.400" wide) (P)
Package Number N24E**

100397 Quad Differential ECL/TTL Translating Transceiver with Latch

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



28-Lead Plastic Chip Carrier (Q)
Package Number V28A

V28A .FEV.1

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